Abstracts

Extracting Small-Signal Model Parameters of Silicon MOSFET Transistors

D. Lovelace, J. Costa and N. Camilleri. "Extracting Small-Signal Model Parameters of Silicon MOSFET Transistors." 1994 MTT-S International Microwave Symposium Digest 94.2 (1994 Vol. II [MWSYM]): 865-868.

A novel approach to the extraction of small signal model parameters for silicon MOSFETs is described. This technique was developed to extract a high frequency model based only on S-parameter measurements to obtain both the intrinsic and parasitic resistance model parameter values of a small signal model.

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